



DMPH4015SK3Q

#### **Product Summary**

BV <sub>DSS</sub>	RDS(ON) Max	<b>Ι</b> <sub>D</sub> T <sub>C</sub> = +25°C
-40V	$11m\Omega @ V_{GS} = -10V$	-45A
-40 v	15mΩ @ $V_{GS}$ = -4.5V	-40A

## **Description and Applications**

This MOSFET has been designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Reverse Polarity Protection
- Motor Control
- Power Management

#### 175°C P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features and Benefits**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)



Top View



Equivalent Circuit

S

П

### Ordering Information (Note 5)

Part Number	Case	Packaging
DMPH4015SK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

D

U U D D

Top View

Pin-Out

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1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

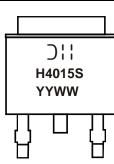
and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

Notes:





# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-40	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
	Steady State	T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C	ID	-45 -35	А
Continuous Drain Current (Note 7) $V_{GS} = -10V$	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +100°C	I <sub>D</sub>	-14 -10	А
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			IDM	-100	А
Maximum Body Diode Forward Current (Note 7)			Is	-5.5	А
Avalanche Current, L = 1mH (Note 8)			I <sub>AS</sub>	-22	А
Avalanche Energy, L = 1mH (Note 8)			E <sub>AS</sub>	260	mJ

#### Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)		PD	1.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{ heta JA}$	73	°C/W
Total Power Dissipation (Note 7)		PD	3.3	W
Thermal Resistance, Junction to Ambient (Note 7) Steady state		$R_{ heta JA}$	38	°C/W
Thermal Resistance, Junction to Case		$R_{ extsf{ heta}JC}$	1.0	C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

## Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)					•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_		-1	μA	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 25 V, V_{DS} = 0 V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.5	-2	-2.5	V	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$	
Static Drain-Source On-Resistance	Deserve		8	11	mΩ	$V_{GS} = -10V, I_D = -9.8A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	11	15	1115.2	$V_{GS} = -4.5V, I_D = -9.8A$	
Diode Forward Voltage	V <sub>SD</sub>	_	-0.7	-1	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>		4234				
Output Capacitance	Coss		1036	—	pF	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		526				
Gate Resistance	R <sub>g</sub>		7.8	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge ( $V_{GS} = -4.5V$ )	Qg	_	42.7	_			
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	91	_	nC	V <sub>DS</sub> = -20V, I <sub>D</sub> = -9.8A	
Gate-Source Charge	Q <sub>gs</sub>	—	14.2	_			
Gate-Drain Charge	$Q_gd$	_	13.5	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	13.2	_			
Turn-On Rise Time	t <sub>R</sub>		10	_		$\label{eq:VGS} \begin{split} V_{GS} &= -10V, \ V_{DD} = -20V, \\ R_G &= 6\Omega, \ I_D = -1A \end{split}$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		303	_	ns		
Turn-Off Fall Time	t <sub>F</sub>		138		]		
Reverse Recovery Time	t <sub>RR</sub>		26	—	ns	I <sub>F</sub> = -9.8A, di/dt = -100A/µs	
Reverse Recovery Charge	Q <sub>RR</sub>		20	_	nC	I <sub>F</sub> = -9.8A, di/dt = -100A/µs	

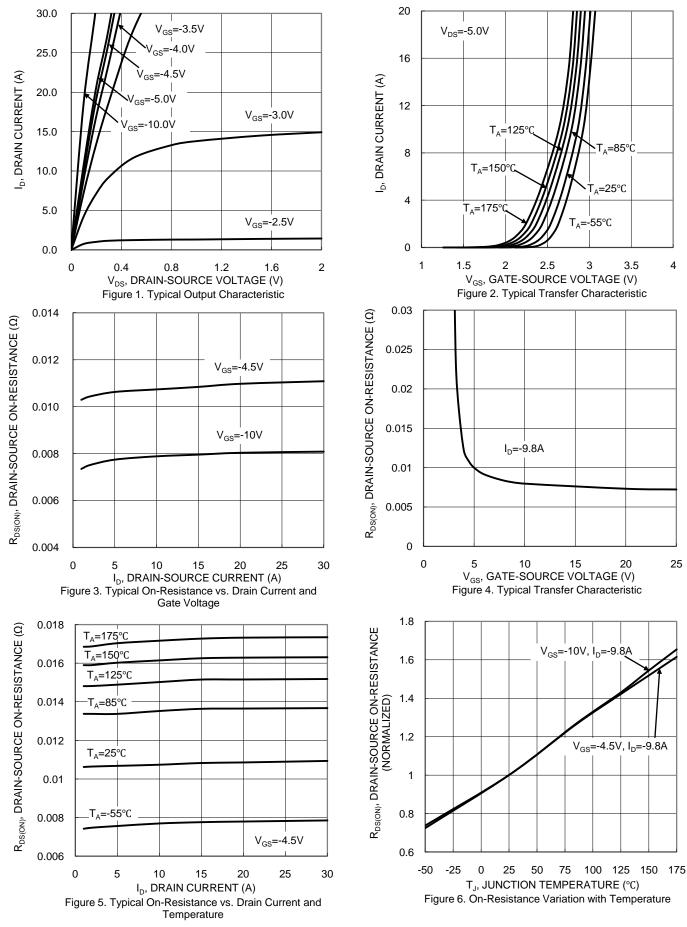
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. Notes:

7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}$ C. 9. Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to product testing.



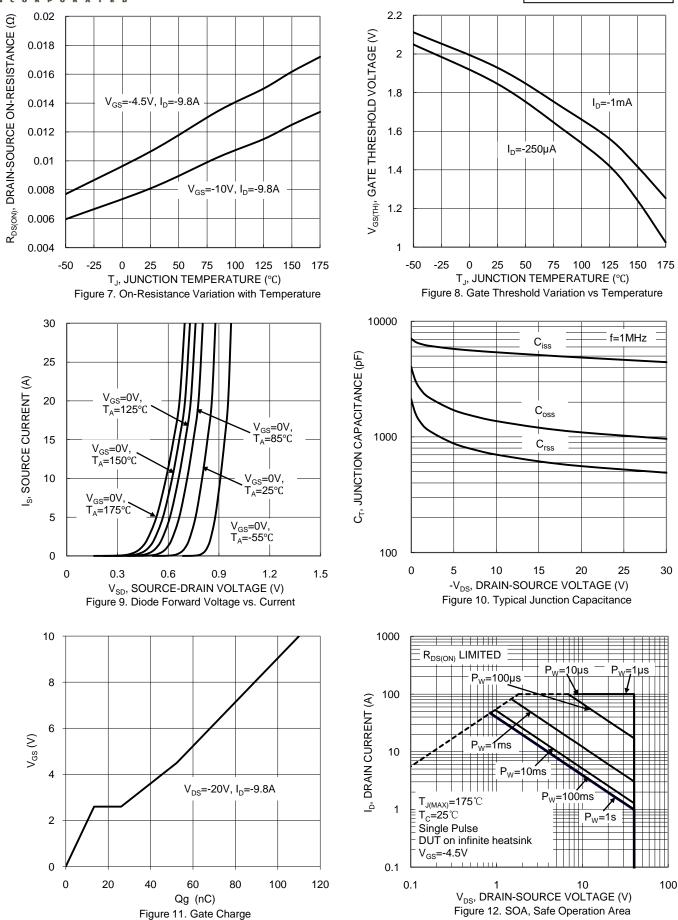
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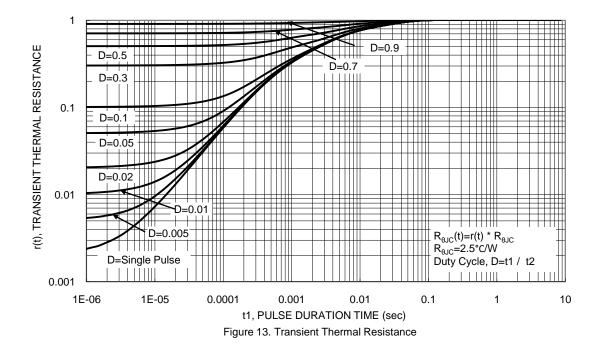


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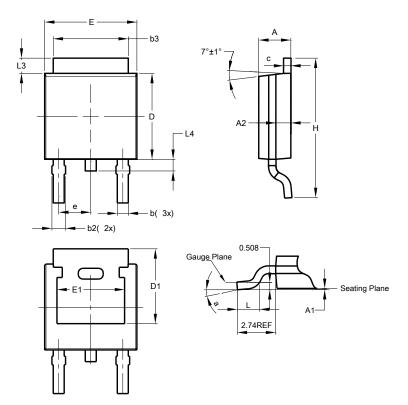






## **Package Outline Dimensions**

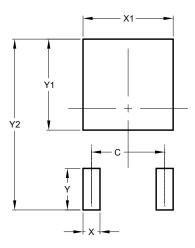
Please see http://www.diodes.com/package-outlines.html for the latest version.



TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Ε	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All	All Dimensions in mm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
С	4.572			
Х	1.060			
X1	5.632			
Y	2.600			
Y1	5.700			
Y2	10.700			



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